THE UNITED STATES PATENT AND TRADEMARK OFFICE

Sir:

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Patent Attorney's Docket No. H1492

In re Patent Application of)						
Bin Yu et al.) Group Art Unit: 2829						
Application No.: 10/653,105) Examiner: S. Geyer						
Filed: September 3, 2003							
For: ADDITIONAL GATE CONTROL FOR A DOUBLE-GATE MOSFET))						
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT TRANSMITTAL LETTER							
U.S. Patent and Trademark Office 220 20 th Street S. Customer Window, Mail Stop Amendment Crystal Plaza Two, Lobby, Room 1B03 Arlington, Virginia 22202							

Enclosed is a Supplemental Information Disclosure Statement and accompanying form

The fee of \$180.00 as set forth in 37 C.F.R. § 1.17(p) is also enclosed.

Charge \$ _____ to Deposit Account No. 50-1070 for the fee due.

A check in the amount of \$ _____ is enclosed for the fee due.

No additional fee for submission of the IDS is required.

A certification under 37 C.F.R. § 1.97(e) is also enclosed.

PTO-1449 for the above-identified patent application.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 50-1070.

Respectfully submitted,

HARRITY & SNYDER, L.L.P.

By:

Glenn Snyder Reg. No. 41,428

11240 Waples Mill Road Suite 300 Fairfax, Virginia 22030 (571) 432-0800

Customer Number: 26615

Date: July 26, 2004



TRADE IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(c)

U.S. Patent and Trademark Office 220 20th Street S. Customer Window, <u>Mail Stop Amendment</u> Crystal Plaza Two, Lobby, Room 1B03 Arlington, Virginia 22202

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(c), applicant(s) bring(s) to the attention of the Examiner the documents listed on the attached PTO 1449. This Supplemental Information Disclosure Statement is being filed after the events recited in Section 1.97(b) but, to the undersigned's knowledge, before the mailing date of either a Final Action or a Notice of Allowance. Under the provisions of 37 C.F.R. § 1.97(c), this Supplemental Information Disclosure Statement:

\boxtimes	includes a certification as specified by Section 1.97(e).		
	is accompanied by a fee of \$180.00 as specified by Section 1.17(p).		

Supplemental Information Disclosure Statement Under 37 C.F.R. § 1.97(c)

Application Serial No. 10/653,105

Attorney's Docket No. H1492

Page 2

Certification 1: Each item of information contained in the Information Disclosure
Statement was first cited in a communication from a foreign patent office in a counterpart
foreign application not more than three months prior to the filing of the Information Disclosure
Statement.
Certification 2: No item of information contained in the Supplemental Information
Disclosure Statement was cited in a communication from a foreign patent office in a counterpart
Disclosure Statement was cited in a communication from a foreign patent office in a counterpart
foreign application, and, to the knowledge of the person signing the certification after making
reasonable inquiry, no item of information contained in the Supplemental Information Disclosure
Statement was known to any individual designated in 37 C.F.R. § 1.56(c) more than three
months prior to the filing date of the Supplemental Information Disclosure Statement.
Copies of the non-patent documents are attached.
Copies of the listed documents were previously submitted in a prior application, serial no, filing date, upon which applicant(s) rely(ies) for the benefits provided in 35 U.S.C. § 120. Applicant(s) respectfully request(s) that the Examiner consider the listed documents and indicate that they were considered by making appropriate notations on the attached form.
The following is a concise statement of relevance of the non-English language
documents.
1 discloses
2 discloses
English translations of the non-English documents are enclosed.
In lieu of a statement of relevance or translation of the non-English documents, an English language version of a search report from the Patent Office in a corresponding application citing these documents and setting forth the relevance thereof is enclosed.

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claims in the application and applicant(s) determine(s) that the cited document(s) do not constitute "prior art" under United States law, applicant(s) reserve(s) the right to present to the office the relevant facts and law regarding the appropriate status of such documents.

Applicant(s) further reserve(s) the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

If any copending application(s) is/are cited on the attached PTO 1449, the Examiner's attention is directed to the foregoing application(s) in compliance with § 2001.06(b) of the Manual of Patent Examining Procedure. By identifying the copending application(s), the assignee and/or applicant of the application(s) do not waive confidentiality of the application(s). Accordingly, the U.S. Patent and Trademark Office is requested to maintain the confidentiality of the copending application(s) under 35 U.S.C. § 122.

If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 50-1070.

Respectfully submitted,

HARRITY & SNYDER, L.L.P.

Bv

Glenn Snyder Reg. No. 41,428

11240 Waples Mill Road Suite 300 Fairfax, Virginia 22030 (571) 432-0800

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INFORMATION DISCLOSURE CITATION

JUL 2 6 2004 H

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ATTORNEY'S DKT NO. APPLICATION NO. 10/653,105

APPLICANT(S)
Bin Yu et al.

FILING DATE
September 3, 2003

GROUP
2829

PTO-1449			September 3, 20		r 3, 2003	2003 2829			
		U.S. PA	TENT DOCU	MENTS					
EXAMINER'S INITIALS	PATENT NO.	DATE	DATE NAME		CLASS	SUBCLASS	1	ING ATE	
	US 2002/0125536 A1	09-12-02	Iwasa et a	Iwasa et al.		368	07-18	07-18-01	
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	US 2002/0177263 A1	11-28-02	Hanafi et a	al.	438	183	05-24	4-01	
	6,359,311 B1	03-19-02	Colinge et al.		257	347	01-17-01		
		FOREIGN F	PATENT DO	CUMENTS					
EXAMINER'S INITIALS	PATENT NO.	DATE	со	UNTRY	CLASS	SUBCLASS	Trans Yes	No No	
	Jong-Tae Park et al.: Transactions on Electrical Fu-Liang Yang et al.: 2002, IEDM, Technical	"Multiple-Ga ron Devices, "25 nm CM	ate SOI MO , Vol. 49, No 10S Omega	SFETs: Dev o. 12, Dece FETs," Inte	vice Design (ember 2002, ernational Ele	Guidelines," , pp. 2222-2 ectron Device	229. es Mee	ting	
	Toshikazu Mukaiyama Anisotropic Etching To 42, No. 7-8, July 8, 1	et al.: "Fal echnique," S 1998, pp. 16	brication of Solid State E 623-1626.	Gate-All-Ar Electronics,	round MOSF Elsevier Sci	ET By Siliconience Publish	n ners, Vo		
	terabit era," Solid State 2002, pp. 1595-1601	te Electronic			-				
	Effendi Leobandung er field-effect transistors International Conferent Nanofabrication in Data Science & Technology 1997, AIP for America	with a sign nce on Electr na Point, CA y B (Microele an Vacuum S	rificant reduction, lon, and A, May 27-3 ectronics an Soc., pp. 27	ction of sho d Photon Bo O, 1997, V d Nanomet 791-2794.	ort channel e eams Techno /ol. 15, No. ter Structure	effects," 41 st ology and 6, <i>Journal o</i> a	f Vacuu	um	
	Toshikazu Mukaiyama Anisotropic Etching Te 42, No. 7-8, July 8, 1 Yang-Kyu Choi et al.: terabit era," Solid State 2002, pp. 1595-1601 Effendi Leobandung et field-effect transistors International Conferent Nanofabrication in Date Science & Technology	et al.: "Fallechnique," Signate Electronical.: "Wire- signate on Electronical. The American Point, CAM y B (Microelectronical)	brication of Solid State E 623-1626. nFET: nanos cs, Elsevier Sechannel and ron, lon, and A, May 27-3 ectronics an Soc., pp. 27	Gate-All-Arelectronics, scale double Science Publication of short on Berry 1997, Value 199	round MOSF, Elsevier Scients CMOS blishers, Volund-gate me ort channel eleams Technological Vol. 15, No. ter Structure	ET By Siliconience Publish S technology 1. 46, No. 10 etal-oxide-sen effects," 41st ology and 6, Journal of	n ner / f), (or the Octol	

EXAMINER DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).